ROITHNER LASERTECHNIK
Wiedner Hauptstraße 76, A-1040 Vienna, Austria
Tel.: ++43 1 586 52 43-0, Fax -44, office@roithner-laser.com

RLT1550-100G

TECHNICAL DATA

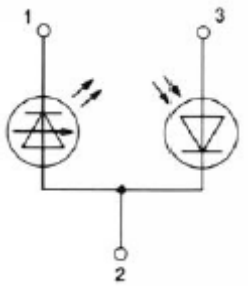


Infrared Laser Diode

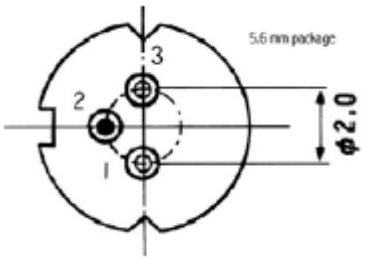
Structure: **GaInAsP/InP, SQW structure**
Lasing wavelength: **typ. 1580 nm, multi mode**
Max. optical power: **100 mW**
Package: **9 mm (SOT-148)**



PIN CONNECTION:



1) Laserdiode cathode
2) Laserdiode anode and photodiode cat
3) Photodiode anode



Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	cw	-	100	-	mW
Threshold Current	I_{th}	cw	300	400	600	mA
Operation Current	I_{op}	P_o = 100 mW	700	800	1000	mA
Operation Voltage	V_{op}	P_o = 100 mW	2.3	2.4	2.5	V
Lasing Wavelength	λ_p	P_o = 100 mW	-	1580	1582	nm
Spectra halfwidth (FWHM)	$\Delta\lambda$	P_o = 100 mW	3	4	6	nm
Beam Divergence	$\Theta_{//}$	P_o = 100 mW	8	10	12	°
Beam Divergence	Θ	P_o = 100 mW	43	45	47	°
Emitting area	Wxd		-	100x 1	-	µm x µm